Supporting Information

Controllable III-V Nanowire Growth via Catalyst Epitaxy

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Figure S1. Thin GaAs NWs grown by using the 0.1 nm thick Pd catalyst film. (a) SEM image, (b) the $PdGa_5$ FFT pattern indexed in Figure 1a, (c) HRTEM and FFT of another $PdGa_5$ catalyst seed.



Figure S2. Typical growth orientations of InGaAs NWs. (a) The <110>-oriented NW and (b) the <111>-oriented NW.